

# **N-Channel General Purpose Amplifier**

This device is designed primarily for low level audio and general purpose applications with high impedance signal sources. Sourced from Process 52.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>DG</sub>	Drain-Gate Voltage	40	V
V <sub>GS</sub>	Gate-Source Voltage	- 40	V
I <sub>GF</sub>	Forward Gate Current	50	mA
T <sub>J</sub> ,T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max U		Units
		J202-203	*MMBFJ202-203	
PD	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

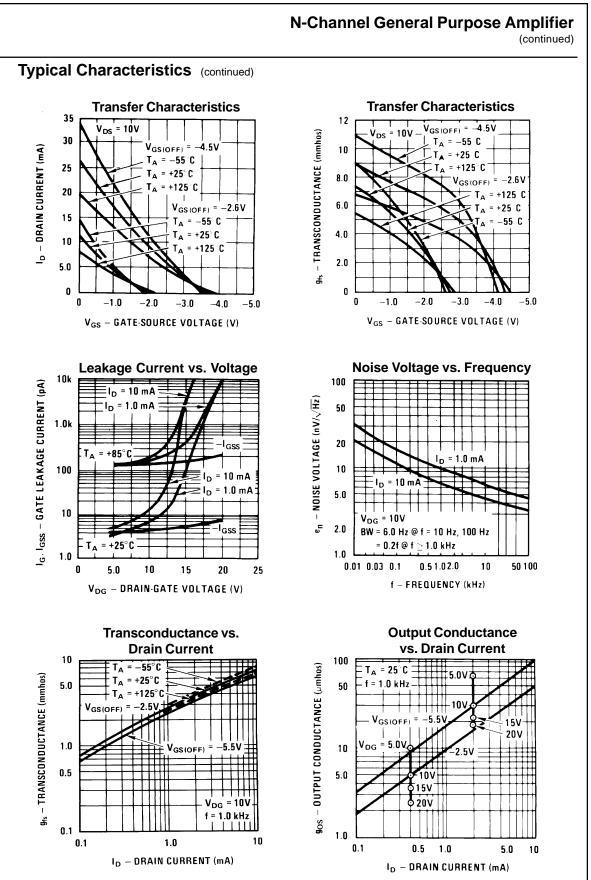
\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

J201 / J202 / MMBFJ201 / MMBFJ202

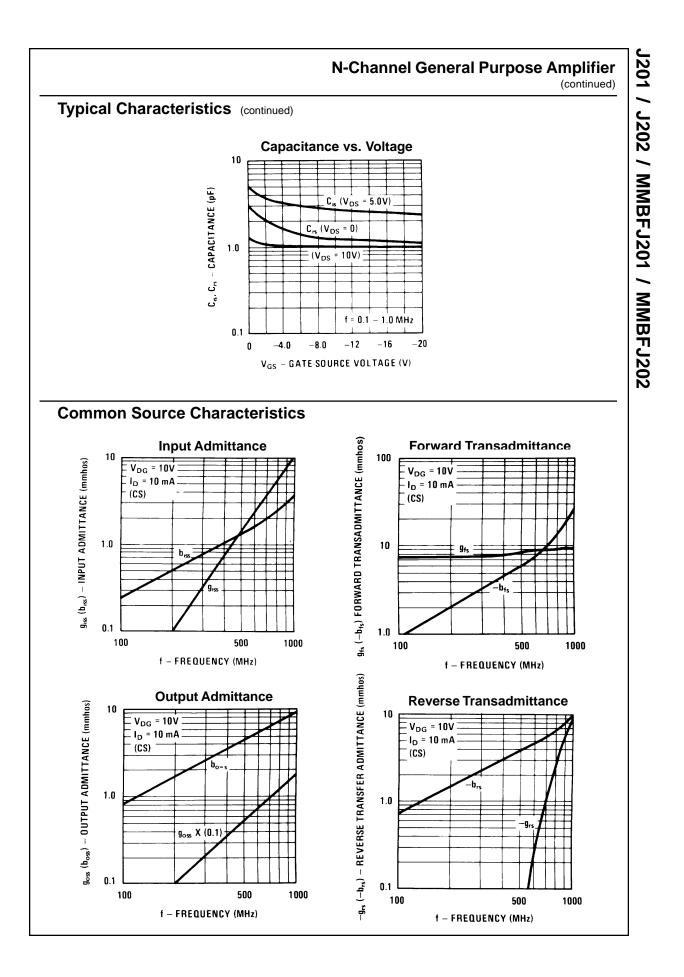
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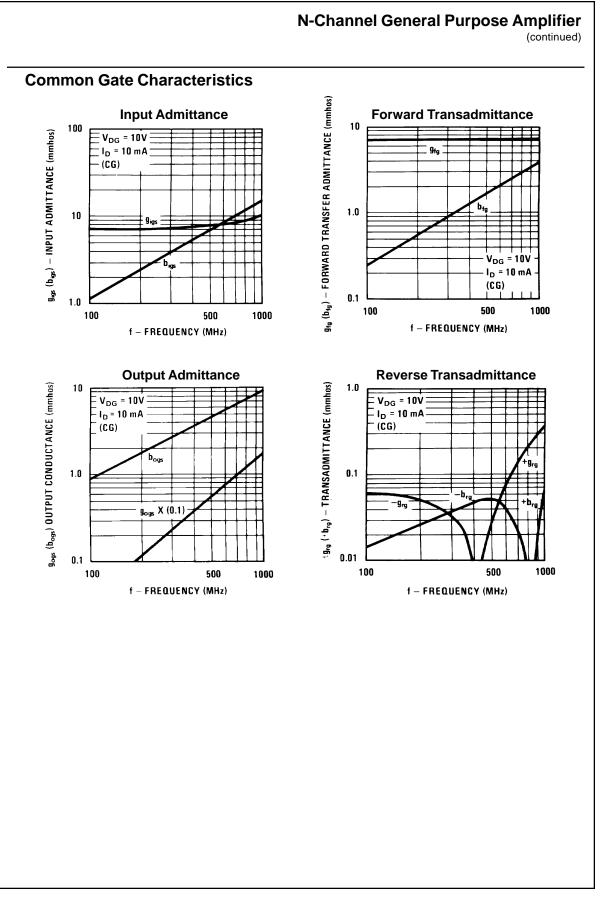
		Test Conditions	Min	Max	Units
	CTERISTICS Gate-Source Breakdown Voltage		- 40		V
	Gate Reverse Current	$I_{G} = -1.0 \ \mu A, \ V_{DS} = 0$ $V_{GS} = -20 \ V, \ V_{DS} = 0$	- 40	-100	pA
/ <sub>GS(off)</sub>	Gate-Source Cutoff Voltage		<b>01</b> - 0.3 <b>02</b> - 0.8	- 1.5 - 4.0	V V
ON CHARAC	CTERISTICS				
	Zero-Gate Voltage Drain Current*	50 / 00	01 0.2 02 0.9	1.0 4.5	mA mA
		• •			
	NAL CHARACTERISTICS Forward Transfer Admittance	V <sub>DS</sub> = 20 V, f = 1.0 kHz 2	<b>01</b> 500		μmhos
			<b>02</b> 1000		μmhos
*Pulse Test: Pulse	e Width ≤ 300 μS Characteristics				
Typical	Characteristics Parameter Interactions	50	mmon Dra	in-Sour	ce
Typical (	Characteristics Parameter Interactions	1000 <sup>50</sup> T. =	<del> </del>		
Typical ( (sorting 50	Characteristics Parameter Interactions	1000 <sup>50</sup> T. =	25°C	V V <sub>G</sub>	s = 0V
Typical (International International Interna	Characteristics Parameter Interactions $g_{\text{fs}}, I_{\text{DSS}} @ V_{\text{DS}} = 10V, V_{\text{GS}} = 0 \text{ PULSED} \\ r_{\text{DS}} @ V_{\text{DS}} = 100 \text{ mV}, V_{\text{GS}} = 0 \text{ PULSED} $	1000 $\overrightarrow{T_A} = \overrightarrow{TYP}$	25°C / <sub>GS(OFF)</sub> = -4.5	V V <sub>G</sub> : -0.5 -1.0V- -	s = 0V
I (mA) NCE (mmhos) 200 200 201 201 201 201 201 201 201 201	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	1000 $\overrightarrow{T_A} = \overrightarrow{TYP}$	25°C / <sub>GS(OFF)</sub> = -4.5	V V <sub>G</sub> : -0.5 -1.0V- -	s = 0V
I (mA) NCE (mmhos) 200 200 201 201 201 201 201 201 201 201	Characteristics Parameter Interactions $g_{fs}, I_{DSS} @ V_{DS} = 10V, V_{GS} = 0$ PULSED $r_{DS} @ V_{DS} = 100 mV, V_{GS} = 0$ $V_{GS(OFF)} @ V_{DS} = 10V, I_D = 1.0 nA$	1000 $\overrightarrow{T_A} = \overrightarrow{TYP}$	25°C / <sub>GS(OFF)</sub> = -4.5	V V <sub>G</sub> : -0.5 	s = 0V
Ince (mmhos) NCE (mmhos) NCE (mmhos)	Characteristics Parameter Interactions $g_{fs}, I_{DSS} @ V_{DS} = 10V, V_{GS} = 0$ PULSED $r_{DS} @ V_{DS} = 100 mV, V_{GS} = 0$ $V_{GS(OFF)} @ V_{DS} = 10V, I_D = 1.0 nA$	1000   50   Table 1     500   0.001   100     500   0.001   100     50   0.001   100     50   0.001   100     50   0.001   100     50   0.001   100     50   0.001   100     50   0.001   100     50   0.001   100	25°C / <sub>GS(OFF)</sub> = -4.5	V V <sub>G</sub> : -0.5 	s = 0V
Loss - DRAIN CURRENT (mA) dis - TRANSCONDUCTANCE (mmhos) 0' 01 02 00 0' 01 01 0' 01 01 0' 01 01 0' 01 01 0' 01 01 0' 01 01 0' 0' 01 01 0' 0' 0' 0' 0' 0' 0' 0' 0' 0' 0' 0' 0' 0	Characteristics Parameter Interactions $g_{fs}, I_{DSS} @ V_{DS} = 10V, V_{GS} = 0$ PULSED $r_{DS} @ V_{DS} = 100 mV, V_{GS} = 0$ $V_{GS(OFF)} @ V_{DS} = 10V, I_D = 1.0 nA$	1000 50 T <sub>A</sub> = 0.0000 0.000 0.000 0.000 0.000 0.000 0.000 0.000 0.000 0.0	25°C / <sub>GS(OFF)</sub> = -4.5	V V <sub>G</sub> : -0.5 	s = 0V
I <sub>coss</sub> – DRAIN CURRENT (mA) B <sub>1s</sub> – TRANSCONDUCTANCE (mmhos) 0 0 01 0 0 01 0 10 0 10	Characteristics Parameter Interactions $g_{fs}$ , $I_{DSS} @ V_{DS} = 10V$ , $V_{GS} = 0$ PULSED $r_{DS} @ V_{DS} = 100$ mV, $V_{GS} = 0$ $V_{GS(DFF)} @ V_{DS} = 10V$ , $I_D = 1.0$ nA $r_{DS}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	25°C / <sub>GS(OFF)</sub> = -4.5	V V <sub>G</sub> -0.5 	s = 0V V +

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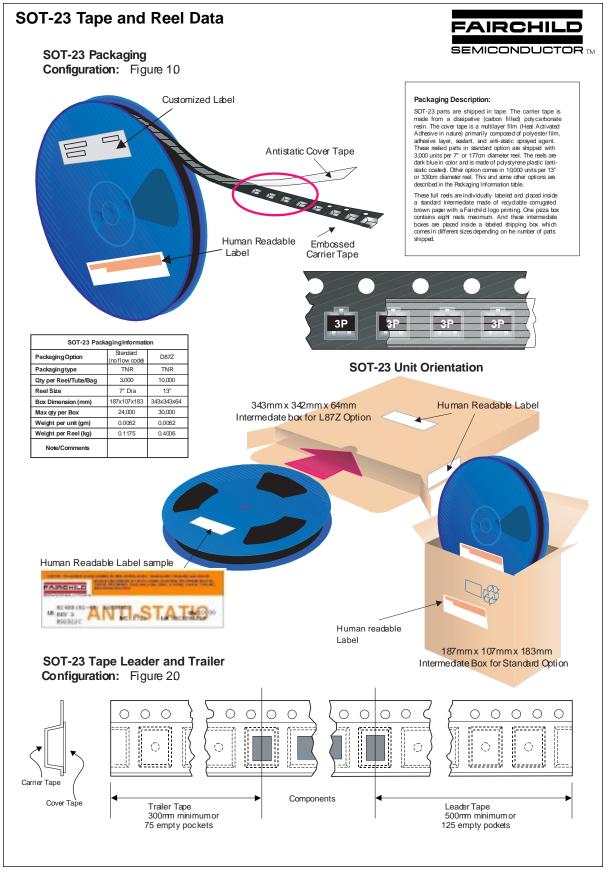
March 2001, Rev. B1





July 1999, Rev. A



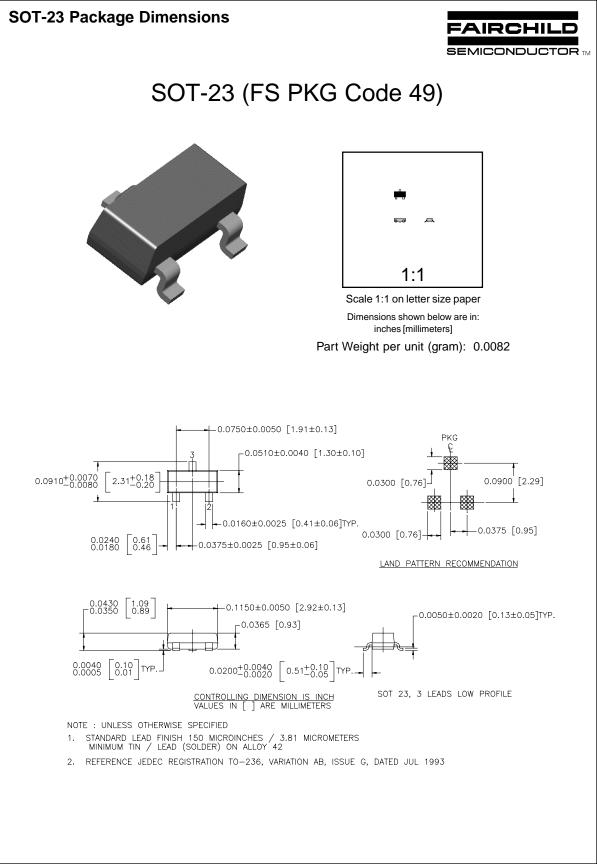


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